

layer so as to be substantially in parallel with each other.

15. (New) The semiconductor device according to claim 14, wherein said at least two signal lines have substantially the same width with said first differential signal lines, and said at least two signal lines are located at positions corresponding to those of said first differential signal lines via said insulating layer in the main part of said semiconductor substrate.

16. (New) The semiconductor device according to claim 14, further comprising second differential signal lines formed via a second insulating layer at sides opposite to those of said first differential signal lines formed via said insulating layer relative to said at least two signal lines.

17. (New) The semiconductor device according to claim 14, wherein said at least two signal lines and said first differential signal lines are substantially in parallel with each other in a main part of said semiconductor substrate.

18. (New) The semiconductor device according to claim 14, wherein the frequency f_0 is 1 GHz or more.--

REMARKS

Favorable consideration of this application as amended is respectfully requested.

In the outstanding Official Action, Claims 1-12 were subjected to restriction. In response, Applicants elect without traverse, and subject to Applicants' right to file a divisional application directed to the non-elected claims, Group I, Claims 1-6, drawn to a semiconductor

device including a signal line, a differential signal line, and a wiring length that is classified in class 257, subclass 798. Thus, in consideration of the present election, Claims 1-6 and 13-18 are presently active in this application, Claims 1 and 4 having been amended and Claims 13-18 added by the present amendment, and Claims 7-12 presumably being withdrawn from consideration by virtue of the present election.

Accordingly, examination on the merits of Claims 1-6 and 13-18 is believed to be in order, and an early and favorable action to that effect is respectfully requested.

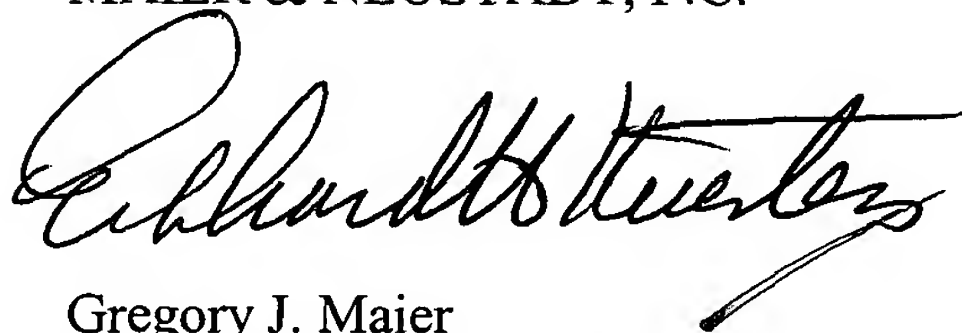
Finally, the attention of the Patent Office is directed to the change of address of Applicants' representative, effective January 6, 2003:

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Respectfully submitted,

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IN THE CLAIMS

2. (Amended) A semiconductor device comprising:

a signal line, [through] which is capable of passing a signal having a desired frequency f_0 [passes] therethrough, formed on a semiconductor substrate; and

a differential signal line through which a signal in opposite phase to said signal passes, or which is connected to a ground power supply,


said signal line and said differential signal line being laminated via an insulating layer so as to be substantially in parallel with each other, and

an actual wiring length l of said signal line being longer than a wiring length l_0 determined by the following equation

$$l_0 = \sqrt{\frac{\frac{L}{C} + \sqrt{\frac{R^2 + 8\pi^2 f_0^2 L^2}{4\pi^2 f_0^2 C^2}}}{R^2 + 4\pi^2 f_0^2 L^2}}$$

where R represents a resistance component, L represents an inductance component, and C represent a capacitance component per unit length of said signal line in such a case that said differential signal line does not exist.

4. (Amended) The semiconductor device according to claim 1, wherein there are at least two of said signal lines, which are formed in the same layer, and a second differential signal line different from said first differential signal line is formed between said at least two



signal lines in the same layer.

Claims 13-18 (New).